SiA461DJ

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Vishay Siliconix





Marking code: BV

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-20				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = -4.5 V	0.033				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = -2.5 V	0.042				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = -1.8 V	0.055				
Q <sub>g</sub> typ. (nC)	18				
I <sub>D</sub> (A) <sup>a</sup>	-12				
Configuration	Single				

#### **FEATURES**

P-Channel 20 V (D-S) MOSFET

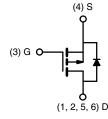
- TrenchFET<sup>®</sup> power MOSFET
- Thermally enhanced PowerPAK<sup>®</sup> SC-70 package
   Small footprint area
   Low on-resistance
- Pb-free RoHS

for definitions of compliance please see <a href="http://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

### APPLICATIONS

Material categorization:

- Smart phones, tablet PCs, mobile computing
  - Battery switch
  - Charger switch
  - Load switch



P-Channel MOSFET

# **ORDERING INFORMATION**

Package	PowerPAK SC-70
Lead (Pb)-free and halogen-free	SiA461DJ-T1-GE3

ABSOLUTE MAXIMUM RATING	$(1_A - 20^{\circ}), 0, 0$	T		LINUT	
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage Gate-source voltage		V <sub>DS</sub>	-20	V	
		V <sub>GS</sub>	± 8		
Continuous drain current ( $T_J = 150 \ ^{\circ}C$ ) Pulsed drain current (t = 300 µs) Continuous source-drain diode current	T <sub>C</sub> = 25 °C		-12 <sup>a</sup>		
	T <sub>C</sub> = 70 °C		-12 <sup>a</sup>		
	T <sub>A</sub> = 25 °C	I <sub>D</sub>	-8.3 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		-6.6 <sup>b, c</sup>	A	
		I <sub>DM</sub>	-20		
	T <sub>C</sub> = 25 °C		-12 <sup>a</sup>		
	T <sub>A</sub> = 25 °C	I <sub>S</sub>	-2.8 <sup>b, c</sup>		
Maximum power dissipation	T <sub>C</sub> = 25 °C		17.9		
	T <sub>C</sub> = 70 °C		11.4	14/	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.4 <sup>b, c</sup>	W	
	T <sub>A</sub> = 70 °C		2.2 <sup>b, c</sup>		
Operating junction and storage temperature range Soldering recommendations (peak temperature) <sup>d, e</sup>		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
		1	260		

#### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL TYPICAL		MAXIMUM	UNIT			
Maximum junction-to-ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	29	37	°C/W		
Maximum junction-to-case (drain)	Steady state	R <sub>thJC</sub>	5.5	7	0/11		

#### Notes

a. Package limited

b. Surface mounted on 1" x 1" FR4 board

c. t = 5 s

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

f. Maximum under steady state conditions is 80 °C/W

S12-0539-Rev. A, 12-Mar-12

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Document Number: 63838

For technical questions, contact: <a href="mailto:pmostechsupport@vishay.com">pmostechsupport@vishay.com</a>

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d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



SiA461DJ

**Vishay Siliconix** 

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	<u> </u>				•		
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-20	-	-	V	
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	-18	-	mV/°C	
V <sub>GS(th)</sub> temperature coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = -250 μΑ	-	3	-		
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	-0.4	-	-1	V	
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$	-	-	± 100	nA	
		$V_{DS} = -20 V, V_{GS} = 0 V$	-	-	-1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	-	-	-10	μA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, \text{ V}_{GS} = -4.5 \text{ V}$	-20	-	-	Α	
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -5.2 \text{ A}$	-	0.025	0.033	Ω	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -4.8 A	-	0.030	0.042		
		V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -2 A	-	0.040	0.055		
Forward transconductance <sup>a</sup>	<b>g</b> fs	$V_{DS} = -6 \text{ V}, \text{ I}_{D} = -5.2 \text{ A}$	-	20	-	S	
Dynamic <sup>b</sup>			1		1		
Input capacitance	C <sub>iss</sub>		-	1300	-	pF	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	210	-		
Reverse transfer capacitance	C <sub>rss</sub>		-	180	-		
•		V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -8 V, I <sub>D</sub> = -5.2 A	-	30	45	nC	
Total gate charge	Qg		-	18	27		
Gate-source charge	Q <sub>gs</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -5.2 A	-	2.1	-		
Gate-drain charge	Q <sub>gd</sub>		-	4.8	-		
Gate resistance	Rg	f = 1 MHz	-	6	-	Ω	
Turn-on delay time	t <sub>d(on)</sub>		-	20	30		
Rise time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, \text{ R}_{\text{I}} = 2.4 \Omega$	-	22	35	_	
Turn-off delay time	t <sub>d(off)</sub>	$I_D \cong -4.2 \text{ A}, V_{\text{GEN}} = -4.5 \text{ V}, R_{\text{g}} = 1 \Omega$	-	50	75	-	
Fall time	t <sub>f</sub>	5	-	20	30	_	
Turn-on delay time	t <sub>d(on)</sub>		-	10	15	- ns	
Rise time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, \text{ R}_{\text{I}} = 2.4 \Omega$	-	12	25		
Turn-off delay time	t <sub>d(off)</sub>	$I_D \cong -4.2 \text{ A}, V_{GEN} = -8 \text{ V}, R_q = 1 \Omega$	-	50	75		
Fall time	t <sub>f</sub>	C C	-	15	25		
Drain-Source Body Diode Characteristi	1 - 1						
Continuous source-drain diode current	Is	T <sub>C</sub> = 25 °C	-	-	-12		
Pulse diode forward current <sup>a</sup>	I <sub>SM</sub>	<u> </u>	-	-	-20	A	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = -4.2 A	-	-0.8	-1.2	V	
Body diode reverse recovery time	t <sub>rr</sub>		-	45	70	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> =-4.2 A, di/dt =100 A/μs,	_	40	60	nC	
Reverse recovery fall time	t <sub>a</sub>	$T_{J} = 25 \text{ °C}$	_	23	-		
Reverse recovery rise time	ta t <sub>b</sub>	~		20		ns	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2\%$ 

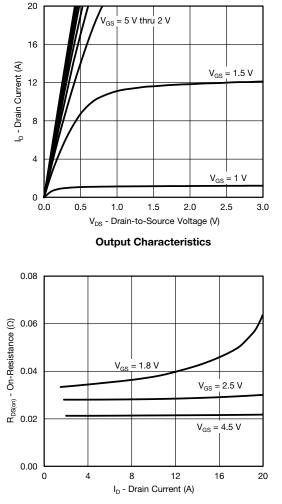
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

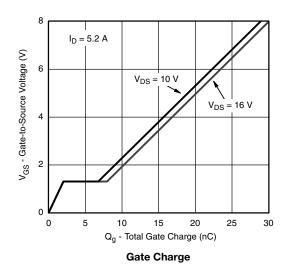
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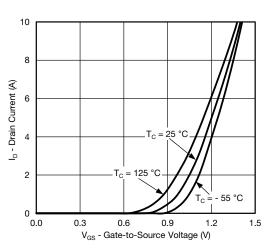


# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

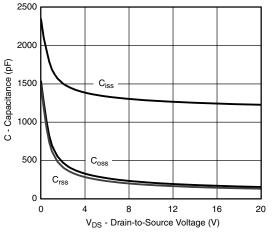


**On-Resistance vs. Drain Current and Gate Voltage** 

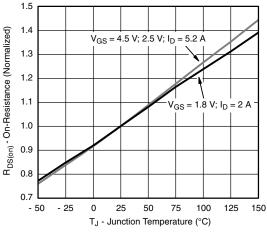




Transfer Characteristics



Capacitance



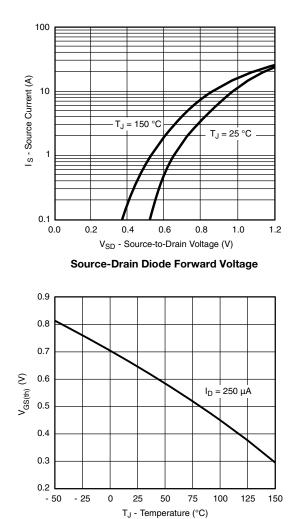
**On-Resistance vs. Junction Temperature** 

3

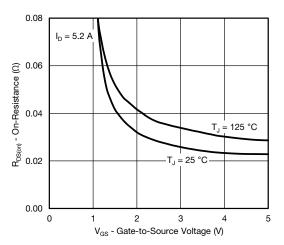
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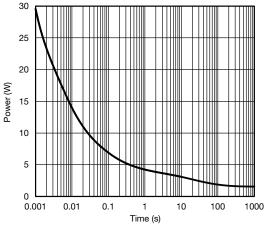
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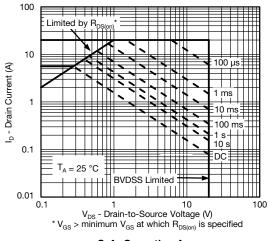
**Threshold Voltage** 



On-Resistance vs. Gate-to-Source Voltage



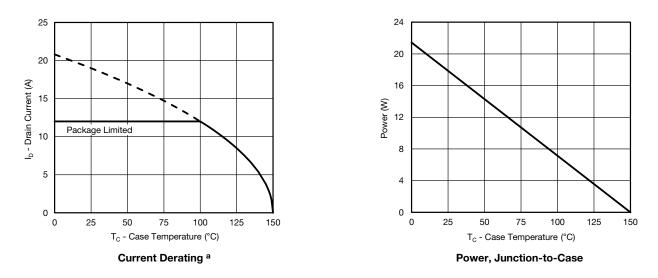




Safe Operating Area



# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

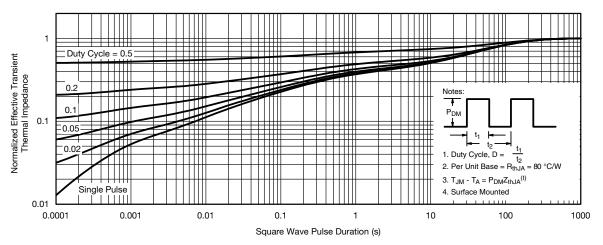


#### Note

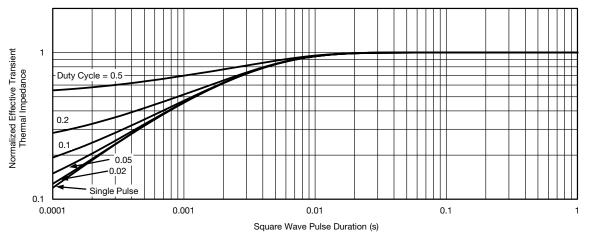
a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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# PowerPAK<sup>®</sup> SC70-6L

VISHA

# b PIN2 PIN1 PIN3 \_ ₹



b

PIN3

\_\_ ₿

PIN2

PIN1

¥

# Vishay Siliconix

<sup>1</sup> 



# RECOMMENDED PAD LAYOUT FOR PowerPAK<sup>®</sup> SC70-6L Single



Dimensions in mm/(Inches)

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